TOSHIBA Transistor Silicon PNP Epitaxial Type (PCT Process)

2SA1934

High-Current Switching Applications

DC-DC Converter Applications

- Low collector saturation voltage: $V_{CE (sat)} = -0.4 \text{ V (max) (IC} = -3 \text{ A)}$
- High-speed switching: $t_{stg} = 1.0 \mu s$ (typ.)
- Complementary to 2SC5176

Absolute Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit	
Collector-base voltage		V _{CBO}	-100	(V)	
Collector-emitter voltage		V _{CEO}	-80	y	
Emitter-base voltage		V _{EBO}	74	V	
Collector current	DC	IC	-5	A	
	Pulse	I _{CP}	(-8)	_ ^	
Base current		I _B	-1	A	
Collector power dissipation		PC	1.8	\\\\\\	
Junction temperature		T _j ((150	°C/	
Storage temperature range		T _{stg}	-55 to 150	°C	

Unit: mm

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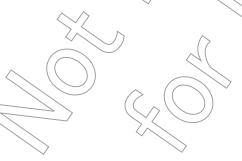
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Weight: 1.5 g (typ.)

Note: Using continuously under heavy loads (e.g. the application of high

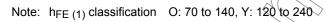
temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

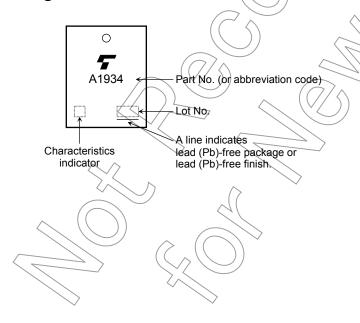


Electrical Characteristics (Ta = 25°C)

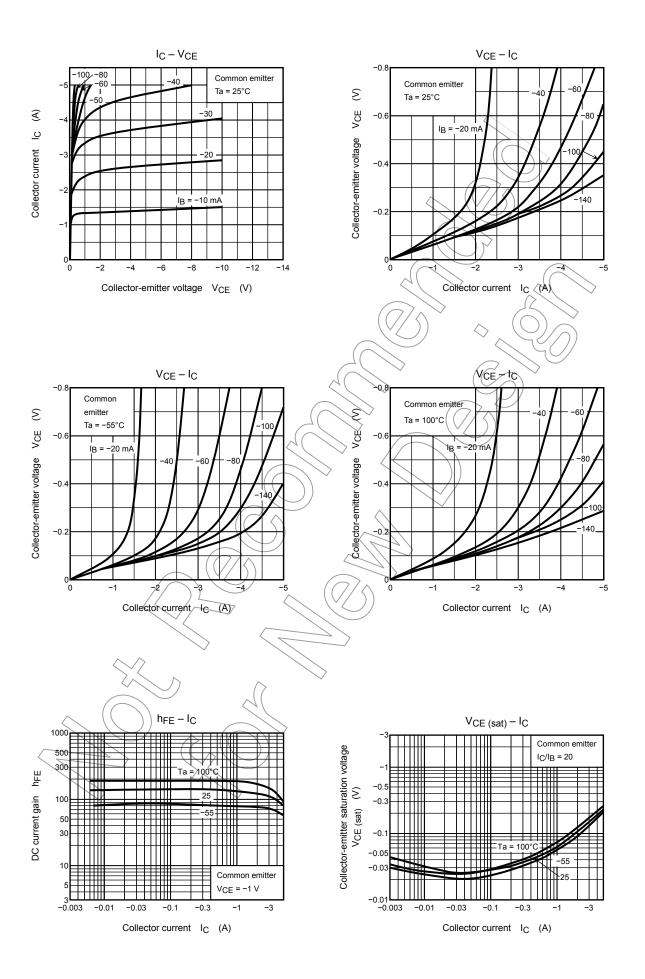
Chara	acteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off of	current	I _{CBO}	V _{CB} = -100 V, I _E = 0	_	_	-1	μΑ
Emitter cut-off cu	rrent	I _{EBO}	V _{EB} = -7 V, I _C = 0	_	_	-1	μΑ
Collector-emitter	breakdown voltage	V (BR) CEO	I _C = -10 mA, I _B = 0	-80	_	_	V
DC current gain		h _{FE (1)} (Note)	V _{CE} = -1 V, I _C = -1 A	70	7	240	
		h _{FE (2)}	V _{CE} = -1 V, I _C = -3 A	40	_	_	
Collector-emitter	saturation voltage	V _{CE (sat)}	$I_C = -3 \text{ A}, I_B = -0.15 \text{ A}$)	-0.2	-0.4	٧
Base-emitter satu	uration voltage	V _{BE} (sat)	$I_C = -3 \text{ A}, I_B = -0.15 \text{ A}$	_	-0.9	-1.2	V
Transition freque	ncy	f _T	V _{CE} = -4 V, I _C = -1 A	_	60	_	MHz
Collector output of	capacitance	C _{ob}	V _{CB} = -10 V, I _E = 0, f = 1 MHz	_	200	_	pF
Switching time	Turn-on time	t _{on}	20 µs Input B22 Output	- (0.2	\\ \rac{1}{\chinnt{\ch	
	Storage time	t _{stg}	IB1 G O O O O O O O O O		\(\frac{1.0}{\cdot 0}\)	_	μs
	Fall time	t _f	$V_{CC} = -30 \text{ V}$ $-I_{B1} = I_{B2} = 0.15 \text{ A, duty cycle} \le 1\%$		0.1	_	

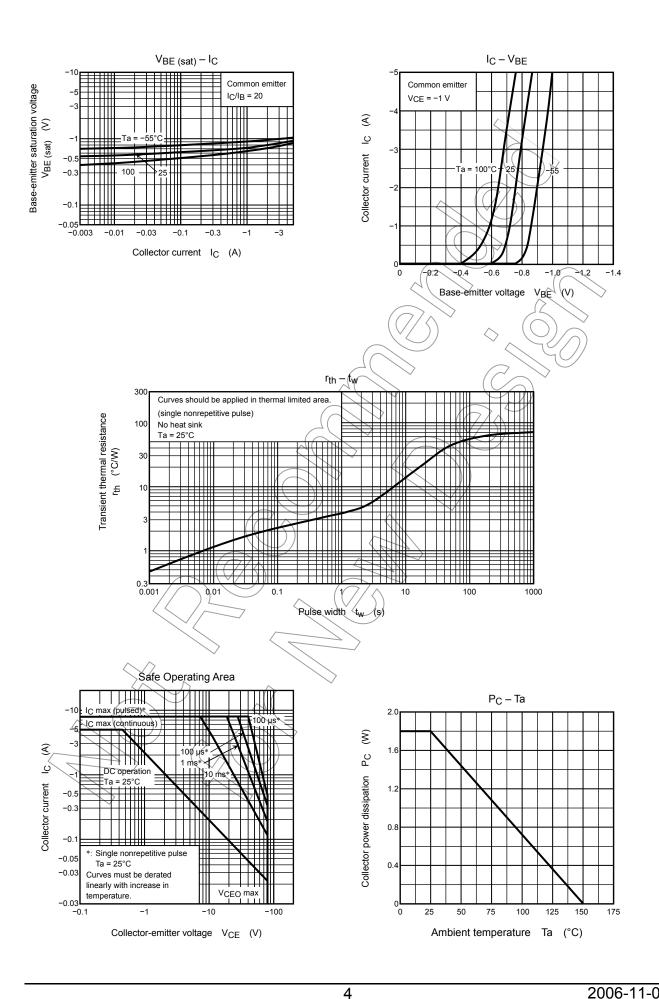






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